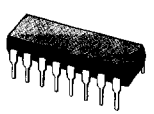
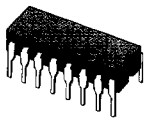
3 TO 8 LINE DECODER/LATCH (INVERTING)

- HIGH SPEED
  t_{PD} = 11 ns (TYP.) AT V_{CC} = 5 V
- LOW POWER DISSIPATION
  I_{CC} = 4 μA (MAX.) AT T_A = 25 °C
- HIGH NOISE IMMUNITY
  $V_{NIH} = V_{NIL}$ = 28 % V_{CC} (MIN.)
- OUTPUT DRIVE CAPABILITY
  10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE
  $|I_{OH}| = I_{OL}$ = 4 mA (MIN.)
- BALANCED PROPAGATION DELAYS
  $t_{PLH} = t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE
  V_{CC} (OPR) = 2 V TO 6 V
- PIN AND FUNCTION COMPATIBLE
  WITH 54/74LS137



B1R
(Plastic Package)



F1R
(Ceramic Package)

M1R
(Micro Package)

C1R
(Chip Carrier)

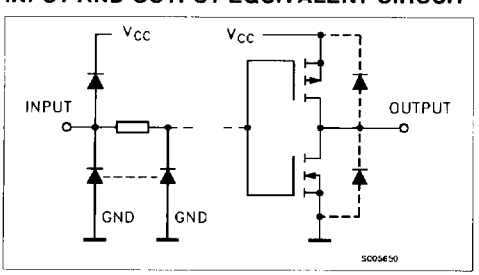
ORDER CODES :

M54HC137F1R M74HC137M1R
M74HC137B1R M74HC137C1R

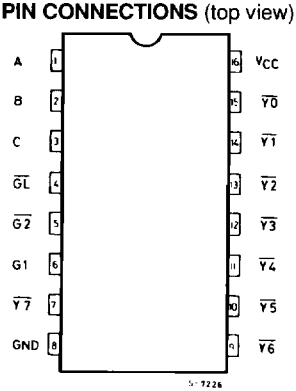
DESCRIPTION

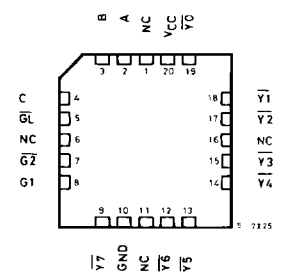
The M54/74HC137 is a high speed CMOS 3 TO 8 LINE DECODER/LATCH (INVERTING) fabricated in silicon gate C^2MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption. This device is a 3 to 8 line decoder with latches on the three address inputs. When $\overline{GL}$ goes from low to high, the address present at the select inputs (A, B and C) is stored in the latches. As long as $\overline{GL}$ remains high no address changes will be recognized. Output enable pins G1 and $\overline{G2}$, control the state of the outputs independently of the select or latch-enable inputs. All the outputs are high unless G1 is high and $\overline{G2}$ is low. The HC137 is ideally suited for the implementation of glitch-free decoders in stored-address applications in bus oriented systems. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN CONNECTIONS (top view)



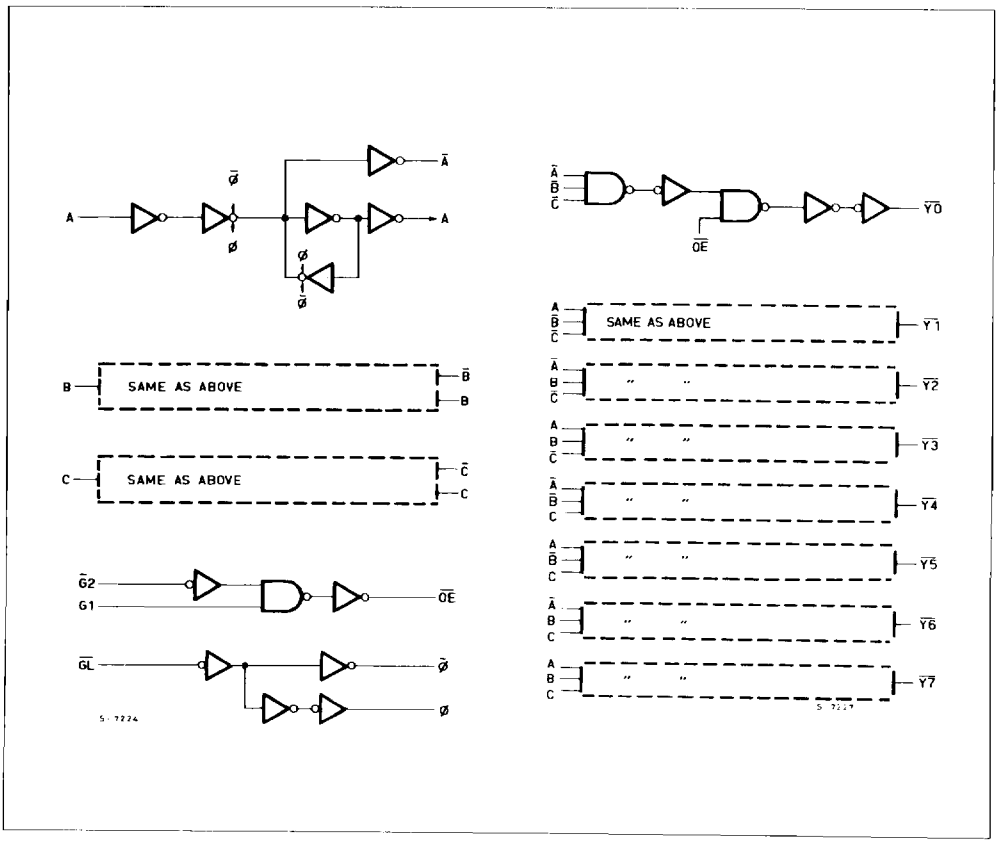


NC = No Internal Connection

TRUTH TABLE

INPUTS						OUTPUTS							
ENABLE			SELECT										
$\overline{GL}$	G1	$\overline{G2}$	C	B	A	$\overline{Y0}$	$\overline{Y1}$	$\overline{Y2}$	$\overline{Y3}$	$\overline{Y4}$	$\overline{Y5}$	$\overline{Y6}$	$\overline{Y7}$
X	X	H	X	X	X	H	H	H	H	H	H	H	H
X	L	X	X	X	X	H	H	H	H	H	H	H	H
L	H	L	L	L	L	L	H	H	H	H	H	H	H
L	H	L	L	L	H	H	L	H	H	H	H	H	H
L	H	L	L	H	L	H	H	L	H	H	H	H	H
L	H	L	L	H	H	H	H	H	L	H	H	H	H
L	H	L	H	L	L	H	H	H	H	L	H	H	H
L	H	L	H	L	H	H	H	H	H	H	L	H	H
L	H	L	H	H	L	H	H	H	H	H	H	L	H
L	H	L	H	H	H	H	H	H	H	H	H	H	L
H	H	L	X	X	X	Outputs corresponding to stored address L: all others H							

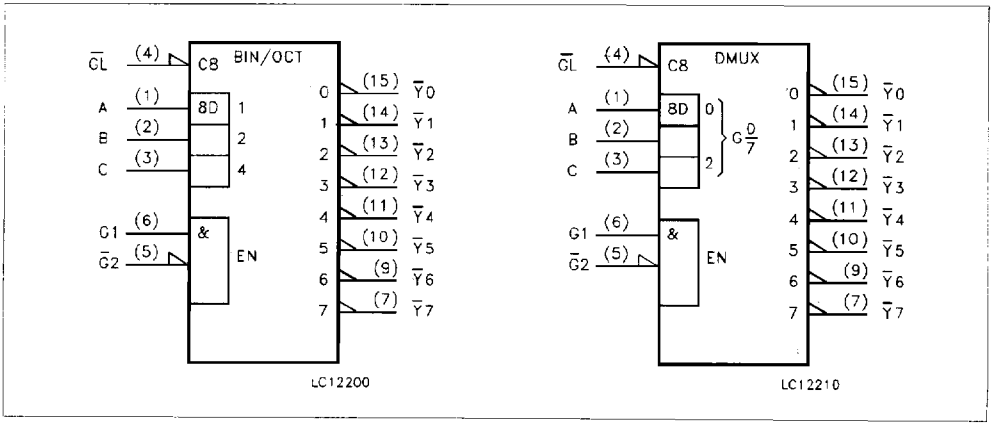
LOGIC DIAGRAM



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 2, 3	A to C	Data Inputs
4	$\overline{GL}$	Latch Enable Input (Active LOW)
5	$\overline{G2}$	Data Enable Input (Active LOW)
6	G1	Data Enable Input (Active HIGH)
15, 14, 13, 12, 11, 10, 9, 7	$\overline{Y0}$ to $\overline{Y7}$	Multiplexer Outputs
8	GND	Ground (0V)
16	V_{CC}	Positive Supply Voltage

IEC LOGIC SYMBOLS



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7	V
V_I	DC Input Voltage	-0.5 to V_{CC} + 0.5	V
V_O	DC Output Voltage	-0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Source Sink Current Per Output Pin	± 25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 50	mA
P_D	Power Dissipation	500 (*)	mW
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.
(*) 500 mW: ≡ 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Value	Unit
V_{CC}	Supply Voltage		2 to 6	V
V_I	Input Voltage		0 to V_{CC}	V
V_O	Output Voltage		0 to V_{CC}	V
T_{op}	Operating Temperature: **M54HC** Series		-55 to +125	°C
	M74HC Series		-40 to +85	°C
t_r, t_f	Input Rise and Fall Time	V_{CC} = 2 V	0 to 1000	ns
		V_{CC} = 4.5 V	0 to 500	
		V_{CC} = 6 V	0 to 400	

DC SPECIFICATIONS

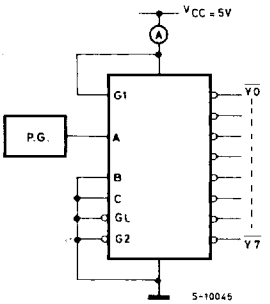
Symbol	Parameter	Test Conditions			Value							Unit
		V_{CC} (V)			T_A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	2.0			1.5			1.5		1.5		V
		4.5			3.15			3.15		3.15		
		6.0			4.2			4.2		4.2		
V_{IL}	Low Level Input Voltage	2.0					0.5		0.5		0.5	V
		4.5					1.35		1.35		1.35	
		6.0					1.8		1.8		1.8	
V_{OH}	High Level Output Voltage	2.0	V_I = V_{IH} or V_{IL}	I_O=-20 µA	1.9	2.0		1.9		1.9		V
		4.5			4.4	4.5		4.4		4.4		
		6.0			5.9	6.0		5.9		5.9		
		4.5		I_O=-4.0 mA	4.18	4.31		4.13		4.10		
		6.0		I_O=-5.2 mA	5.68	5.8		5.63		5.60		
V_{OL}	Low Level Output Voltage	2.0	V_I = V_{IH} or V_{IL}	I_O= 20 µA		0.0	0.1		0.1		0.1	V
		4.5				0.0	0.1		0.1		0.1	
		6.0				0.0	0.1		0.1		0.1	
		4.5		I_O= 4.0 mA		0.17	0.26		0.33		0.40	
		6.0		I_O= 5.2 mA		0.18	0.26		0.33		0.40	
I_I	Input Leakage Current	6.0	V_I = V_{CC} or GND				±0.1		±1		±1	µA
I_{CC}	Quiescent Supply Current	6.0	V_I = V_{CC} or GND				2		20		40	µA

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input $t_r = t_f$ = 6 ns)

Symbol	Parameter	Test Conditions		Value							Unit
		V_{CC} (V)		T_A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t_{TLH} t_{THL}	Output Transition Time	2.0			30	75		95		110	ns
		4.5			8	15		19		22	
		6.0			7	13		16		19	
t_{PLH} t_{PHL}	Propagation Delay Time (G1 - $\overline{Y}$)	2.0			45	115		145		175	ns
		4.5			14	23		29		35	
		6.0			12	20		25		30	
t_{PLH} t_{PHL}	Propagation Delay Time ($\overline{G2}$ - $\overline{Y}$)	2.0			50	115		145		175	ns
		4.5			15	23		29		35	
		6.0			13	20		25		30	
t_{PLH} t_{PHL}	Propagation Delay Time ($\overline{GL}$ - $\overline{Y}$)	2.0			70	170		215		250	ns
		4.5			22	34		43		50	
		6.0			19	29		37		43	
t_{PLH} t_{PHL}	Propagation Delay Time (A, B, C - $\overline{Y}$)	2.0			70	165		205		110	ns
		4.5			21	33		41		22	
		6.0			18	28		35		19	
$t_{W(L)}$	Minimum Pulse Width ($\overline{GL}$)	2.0			12	50		65		75	ns
		4.5			3	10		13		15	
		6.0			3	9		11		13	
t_s	Minimum Set-up Time (A, B, C - $\overline{GL}$)	2.0			8	50		60		75	ns
		4.5			2	10		12		15	
		6.0			2	9		10		13	
t_h	Minimum Hold Time (A, B, C - $\overline{GL}$)	2.0				5		5		5	ns
		4.5				5		5		5	
		6.0				5		5		5	
C_{IN}	Input Capacitance				5	10		10		10	pF
C_{PD} (*)	Power Dissipation Capacitance				55						pF

(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operting current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

TEST CIRCUIT I_{CC} (Opr.)



INPUT WAVEFORM IS THE SAME AS THAT IN CASE OF SWITCHING CHARACTERISTICS TEST.

TYPICAL APPLICATION